



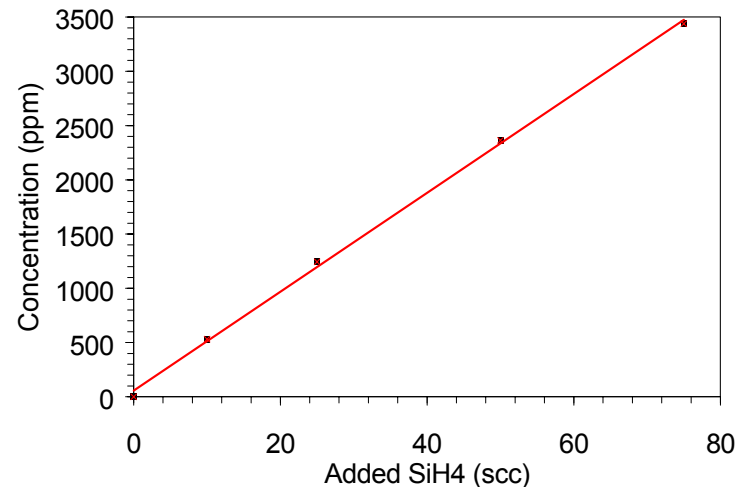
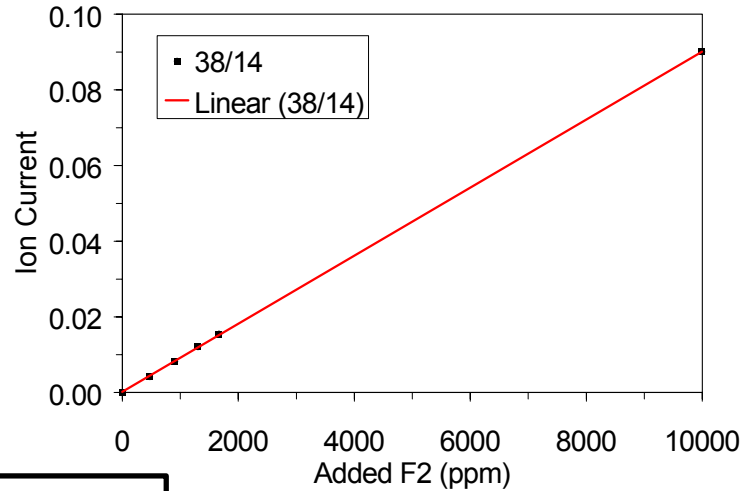
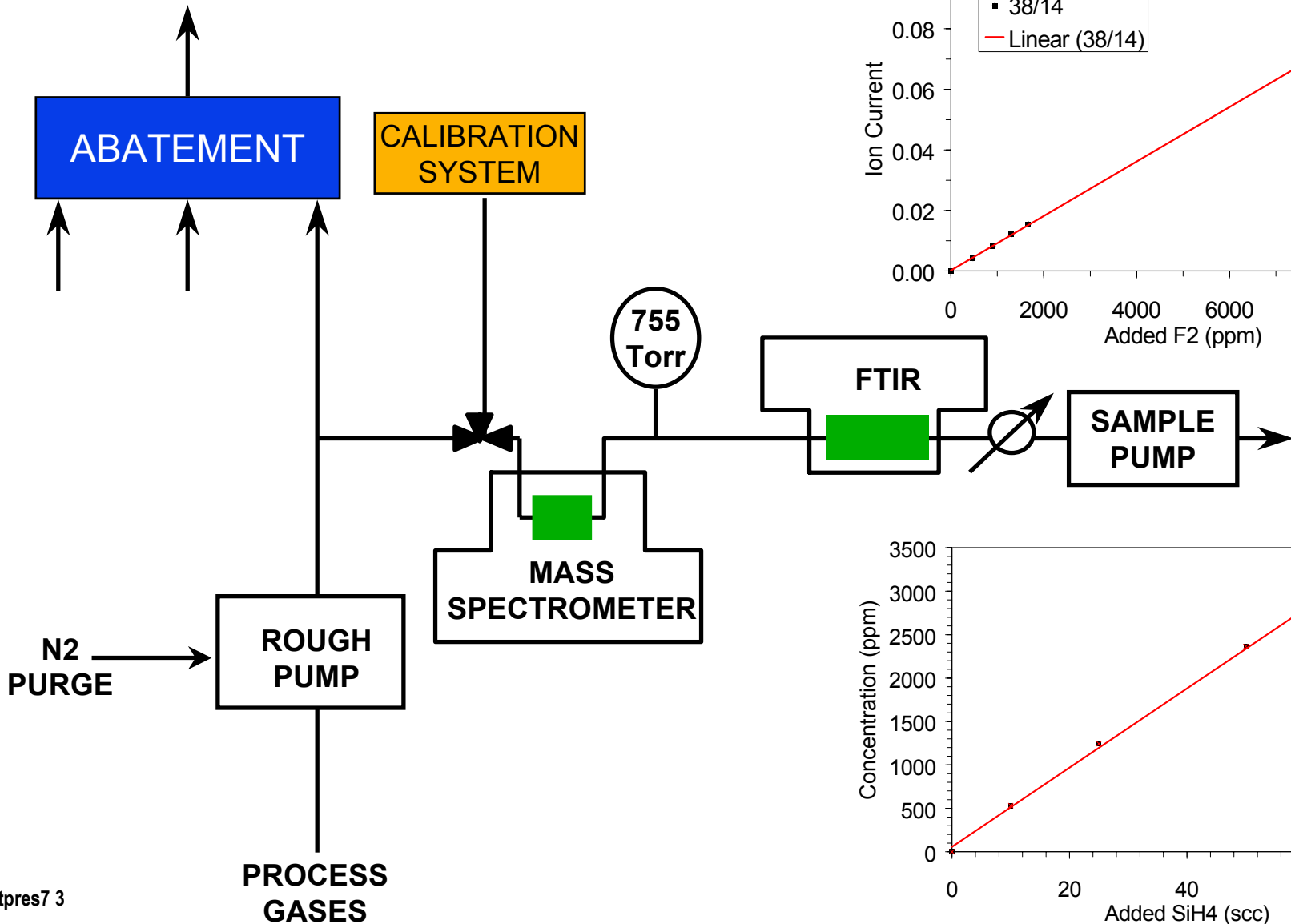
MINIMIZING PFC AND HAP EMISSIONS DURING ULTIMA HDP-CVD PROCESSING: PSG, USG, AND FSG FILMS

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Air Products and Chemicals, Inc..

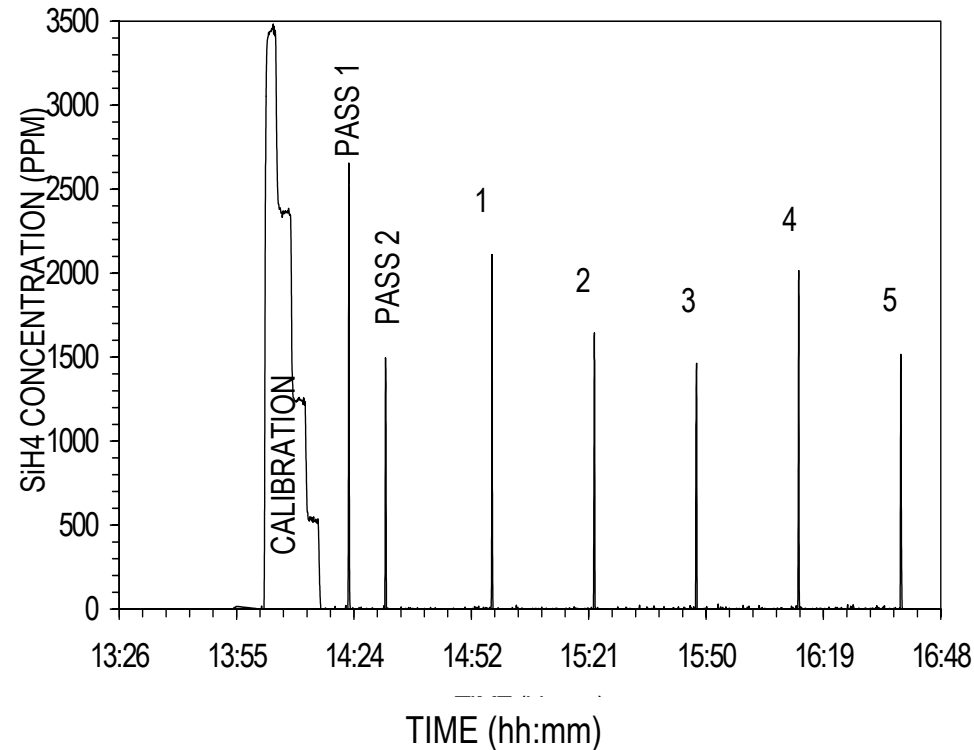
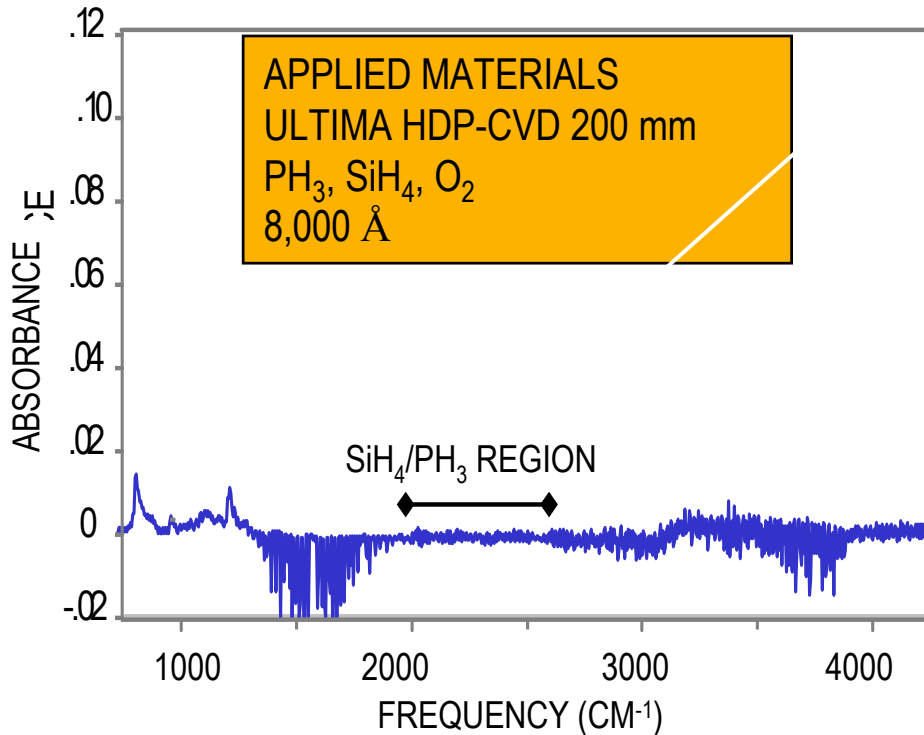
Mat Waltrip, Thanh Pham, Patricia
Jennings, and Jack Branning
Applied Materials, Inc..

SEMICONDUCTOR PROCESS EMISSIONS

- GASES OF CONCERN
 - PFCs: CF_4 , C_2F_6 , C_3F_8 , NF_3
 - HAPs: HF , F_2
 - VOCs
- DETERMINE PROCESS EMISSIONS
 - ANALYTICAL METHODOLOGY
- MINIMIZE PFC AND HAP EMISSIONS
 - ULTIMA HDP-CVD: PSG, USG, AND FSG
 - REMOTE NF_3 CLEAN TECHNOLOGY
 - DELATECH CDO ABATEMENT



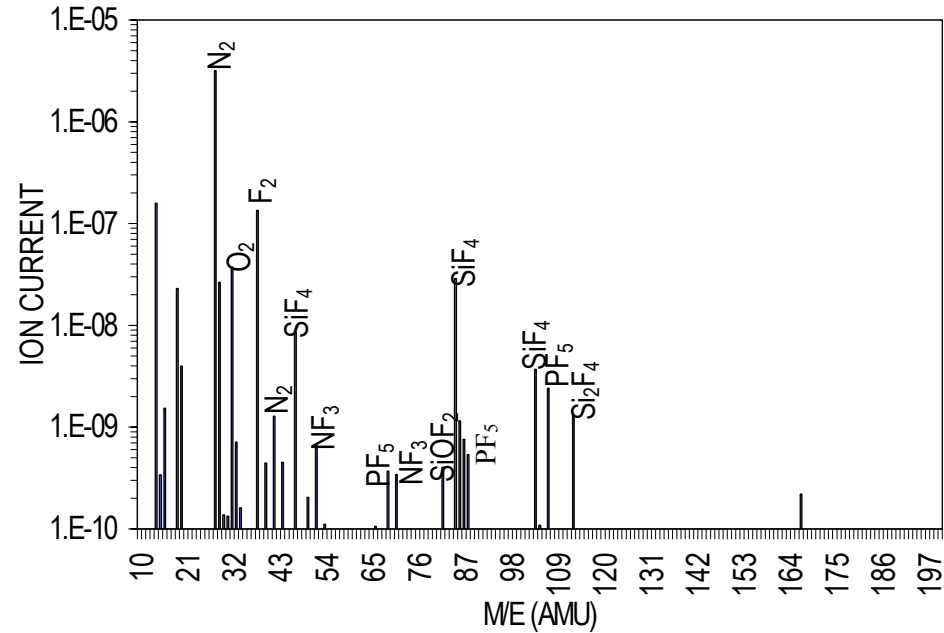
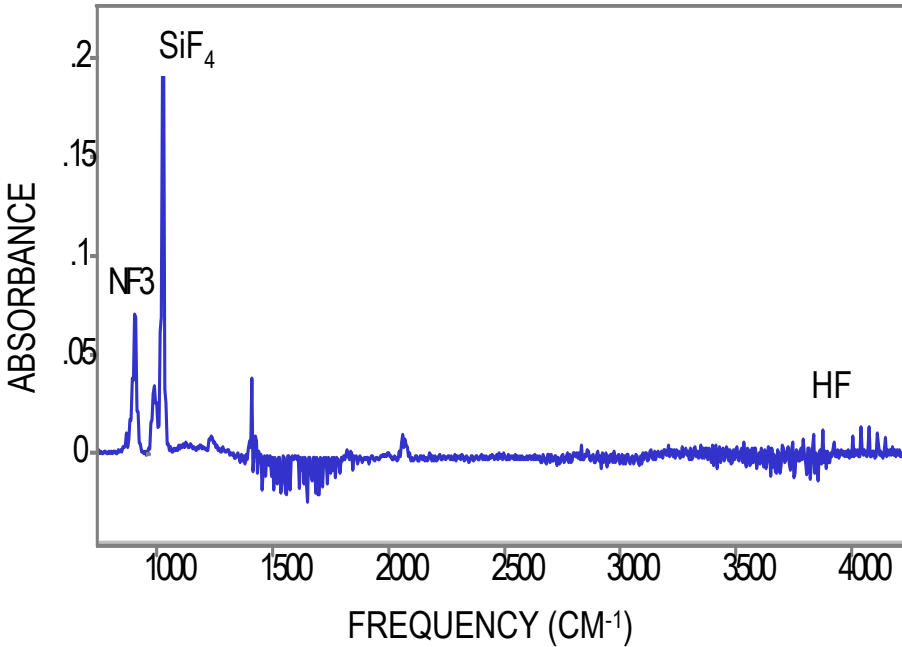
ULTIMA HDP-CVD: PSG DEPOSITION



- SiH₄ AND PH₃ PROCESS GASES FULLY UTILIZED

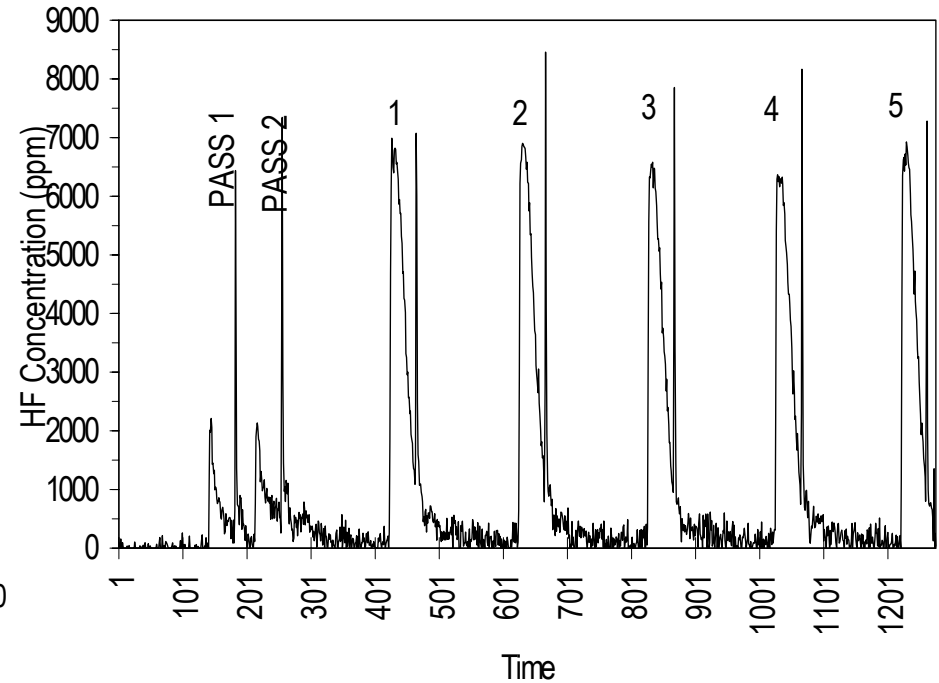
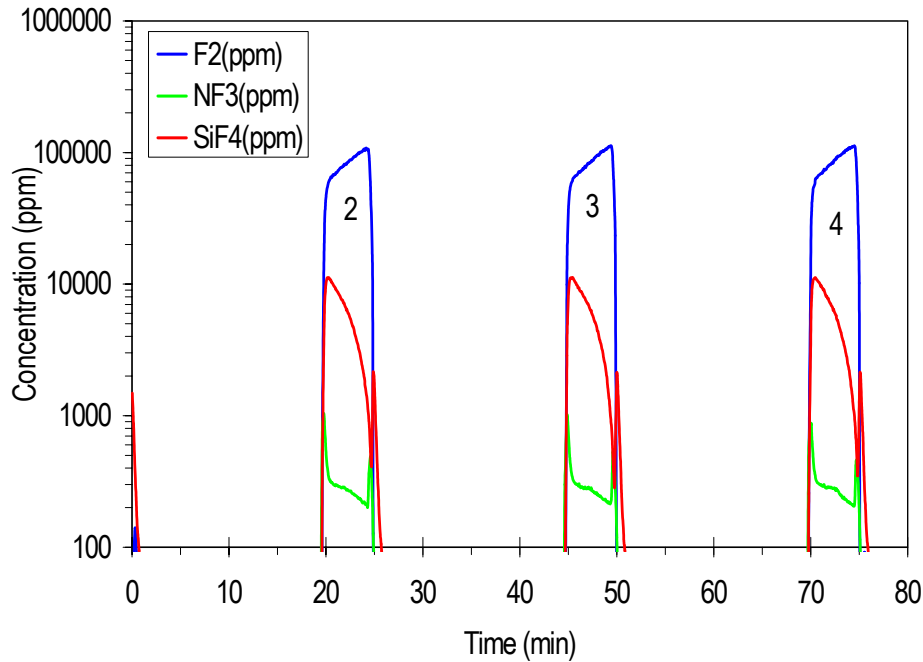
- NO OTHER BYPRODUCTS

ULTIMA HDP-CVD: PSG CHAMBER CLEAN



- IDENTIFY CLEAN BYPRODUCTS
 - NF₃, SiF₄, F₂, PF₅, HF, O₂

CONCENTRATION PROFILE: ULTIMA HDP-CVD PSG CLEAN

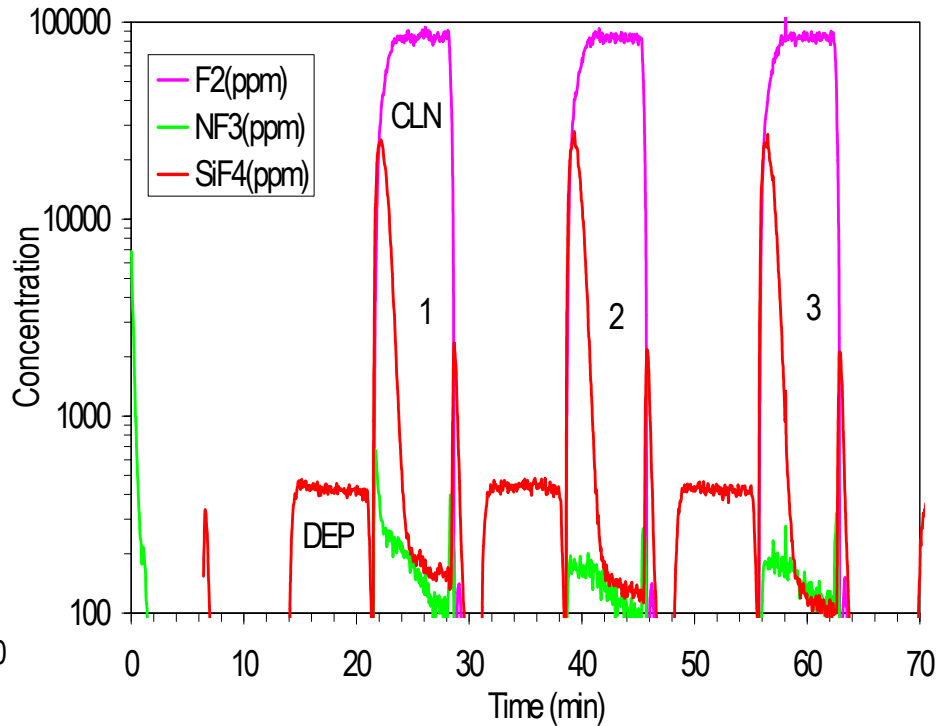
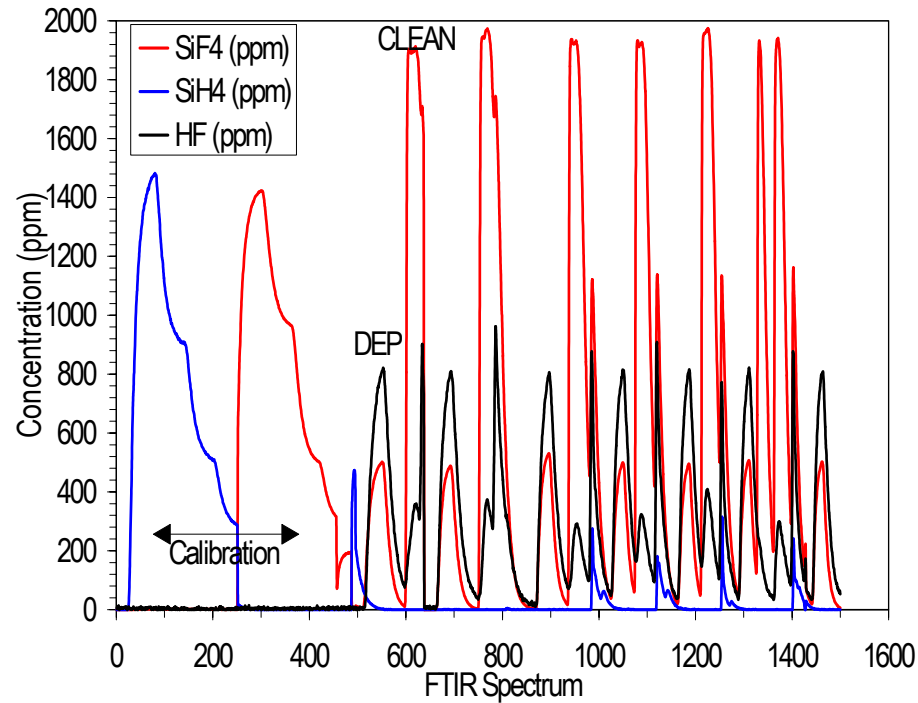


- VOLUMETRIC EMISSIONS
 - INTEGRATE UNDER PROFILE
 - MULTIPLY BY PUMP PURGE (22.8 SLM)

VOLUMETRIC EMISSIONS

	<u>PSG CLEAN</u>						AVE
	PASS1	PASS2	1	2	3	4	(scc)
<i>NF3(scc)</i>	60	41	44	39	38	37	39
<i>SiF4(scc)</i>	73	60	687	672	662	651	668
<i>PF5</i>	4	3	34	34	33	33	33
<i>F2(scc)</i>	8153	9668	7707	8670	8908	8940	8556
<i>HF(scc)</i>	122	189	547	539	520	510	529
<u><i>Utilization (%)</i></u>	99	99	99	99	99	99	99
<u><i>F-Balance</i></u>	0.79	0.93	0.89	0.98	0.99	1.00	0.96
	<u>PSG DEP</u>						AVE
	PASS1	PASS2	1	2	3	4	(scc)
<i>SiH4(scc)</i>	0	0	0	0	0	0	0
<i>PH3(scc)</i>	0	0	0	0	0	0	0

ULTIMA HDP-CVD: FSG DEPOSITION AND CLEAN



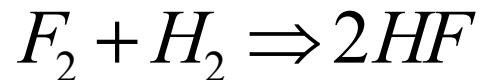
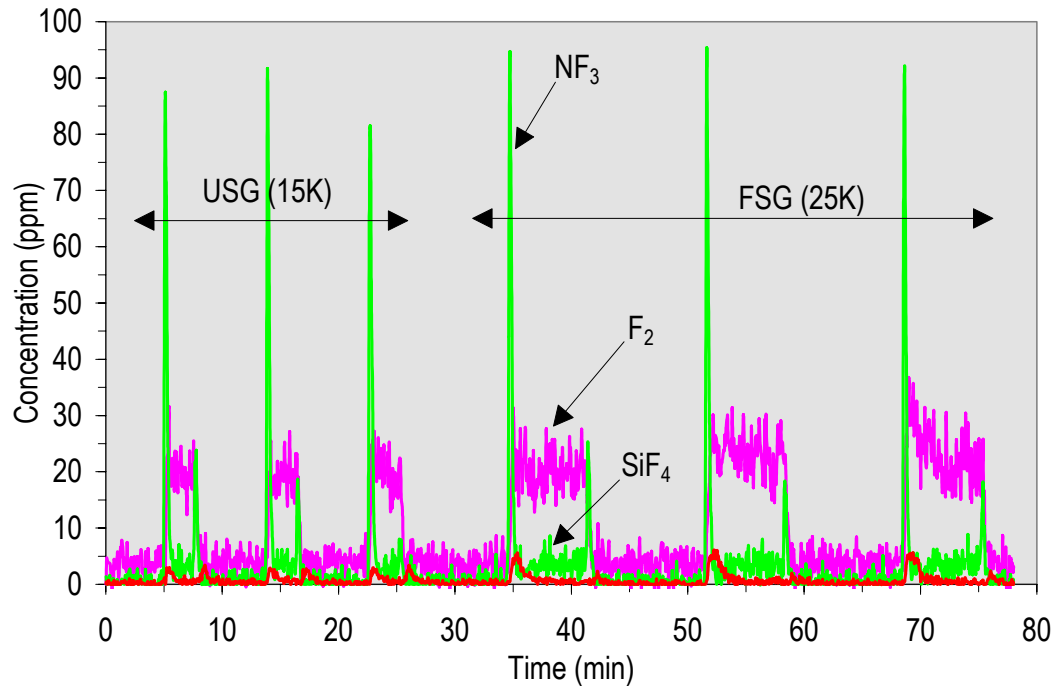
- DEPOSITION BYPRODUCTS
 - HF, SiF₄
- CLEAN BYPRODUCTS
 - F₂, SiF₄, NF₃

VOLUMETRIC EMISSIONS: ULTIMA HDP-CVD FSG

DEP (scc)	1	2	3	4	5	6	7	8	9	10	11	12	13
SiF ₄	37	29	35	39	29		30	28	38	55	34	34	53
HF	62	54	53	57	50		53	50	54	56	47	49	58
SiH ₄	4	0	0	3	0		0	0	0	0	0	0	1

CLEAN (scc)	1	2	3	AVE
<i>NF₃</i>	40	27	29	32
<i>SiF₄</i>	793	849	817	820
<i>F₂</i>	13,559	13,443	13,562	13,522
<i>HF</i>	99	99	99	99
<i>F-Balance</i>	<u>1.00</u>	<u>1.00</u>	<u>1.00</u>	<u>1.00</u>
<i>Utilization (%)</i>	<u>99.6</u>	<u>99.7</u>	<u>99.7</u>	<u>99.7</u>

PROCESS ABATEMENT: DELATECH CDO



- MEASUREMENTS DOWNSTREAM OF THE DELATECH
 - MONITOR PROCESS BYPRODUCTS
 - TOTAL GAS FLOW 177 SLM

FLUORINE REMOVAL EFFICIENCY

	USG (15 kA)		FSG (25 kA)	
	<i>BEFORE CDO</i>	<i>AFTER CDO</i>	<i>BEFORE CDO</i>	<i>AFTER CDO</i>
NF₃ (scc)	22	7	32	10
SiF₄ (scc)	249	1	820	2
F₂ (scc)	7,056	13	13,522	31
HF (scc)	100	n/a	100	n/a

- F₂ EFFICIENTLY CONVERTED TO HF
- HF EFFICIENTLY SCRUBBED
- FLUORINE EMISSIONS REDUCED 99.8 %

SUMMARY

- QUANTITATIVE ANALYSIS OF ULTIMA HDP-CVD PROCESSES
 - PSG DEPOSITION AND CLEAN
 - USG DEPOSITION AND CLEAN
 - FSG DEPOSITION AND CLEAN
- REMOTE NF_3 CLEAN ELIMINATES PFC EMISSIONS
 - MMTCE $0.15 \cdot 10^{-9}$
 - PROCESS BENEFITS
- DELATECH CDO REMOVES 99.8 % FLUORINE INFLUENT